RT1N141X SERIES

〈Transistor〉 Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

UNIT:mm

OUTLINE DRAWING

DESCRIPTION

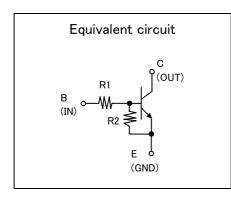
RT1N141X is a one chip transistor with built-in bias resistor,PNP type is RT1P141X.

FEATURE

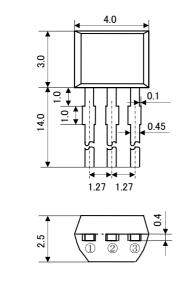
www.DataSheet4U.**Built-in bias resistor** (R1=10k Ω ,R2=10k Ω).



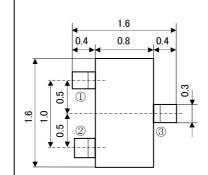
Inverted circuit, switching circuit, interface circuit, driver circuit.







JEITA: --JEDEC: Terminal Connector ①:Emitter ②:Collector ③:Base



0.1

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JEITA : -

JEDEC : -

Terminal Connector

1):Base

2: Emitter

3: Collector

RT1N141M

2.1

1.25

0.425

0.3

0.425

1

0.65

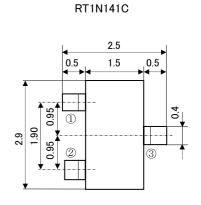
0.65

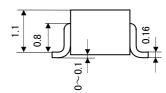
2.0

0.9

0.7

RT1N141U





JEITA : SC-59 JEDEC : Similar to TO-236

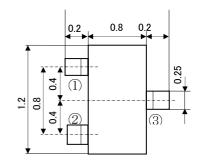
Terminal Connector

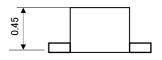
①:Base

2:Emitter

3: Collector

RT1N141T





JEITA: — JEDEC: — Terminal Connector ①:Base ②:Emitter ③:Collector

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JEITA: SC-70

Terminal Connector

JEDEC: -

1):Base

2:Emitter

3: Collector

www.DataSheet4U.com

RT1N141X SERIES

〈Transistor〉

Transistor With Resistor

For Switching Application

Silicon NPN Epitaxial Type

MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING					
		RT1N141T	RT1N141U	RT1N141M	RT1N141C	RT1N141S	UNIT
V _{CBO}	Collector to Base voltage	50					V
V _{EBO}	Emitter to Base voltage	10					V
V _{CEO}	Collector to Emitter voltage	50					V
Ι _c	Collector current	100					mA
I _{CM}	Peak Collector current	200					mA
Б	Collector	125(※)	125	150	50	450	mW
4U.con Pc	dissipation(Ta=25°C)	125(%)	125	1.	50	450	TTIVV
Tj	Junction temperature	+125		+150			°C
Tstg	Storage temperature	-55~+125		-55~+150			°C

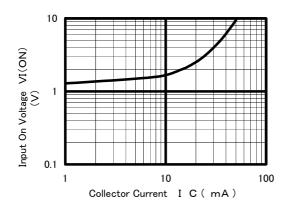
(※) package mounted on 9mm×19mm×1mm glass-epoxy substrate.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

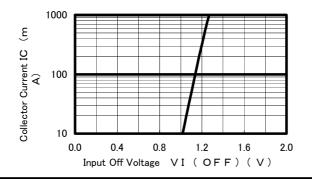
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	$I_{c}=100 \mu A, R_{BE}=\infty$	50			V
I _{CBO}	Collector cut off current	V _{CB} =50V, I _E =0			0.1	μA
h _{FE}	DC forward current gain	V _{CE} =5V, I _c =10mA	50			—
V _{CE(sat)}	C to E saturation voltage	I _c =10mA, I _B =0.5mA		0.1	0.3	V
V _{I(ON)}	Input on voltage	V _{CE} =0.2V, I _c =5mA		1.5	3.0	V
V _{I(OFF)}	Input off voltage	V_{CE} =5V, I _c =100 μ A	0.8	1.1		V
R ₁	Input resistance		7.0	10	13	kΩ
R_2 / R_1	Resistance ratio		0.9	1.0	1.1	
f _T	Gain band width product	V_{ce} =6V, I _e =-10mA		200		MHz

TYPICAL CHARACTERISTICS

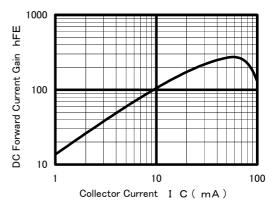
Input On Voltage - Collector Current







DC Forward Current Gain - Collector Current



ISAHAYA ELECTRONICS CORPORATION



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